\*\* Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

**Vishay Semiconductors** 

VSLY5850

### High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology

### **FEATURES**

- · Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- · Leads with stand-off
- Peak wavelength:  $\lambda_p = 850 \text{ nm}$
- High reliability
- · High radiant power
- · High radiant intensity
- Narrow angle of half intensity:  $\varphi = \pm 3^{\circ}$
- · Suitable for high pulse current operation
- Good spectral matching with CMOS cameras
- · Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

#### **APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- · High speed IR data transmission
- Smoke-automatic fire detectors
- IR Flash

## DESCRIPTION

VSLY5850 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with extreme high radiant intensity, high optical power and high speed, molded in a clear, untinted plastic package, with a parabolic lens.

**PRODUCT SUMMARY** COMPONENT Ie (mW/sr) φ (deg)  $\lambda_p$  (nm) t<sub>r</sub> (ns) VSLY5850 850 600 ± 3 10

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING REMARKS PACKAG		PACKAGE FORM			
VSLY5850	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾			

Note

· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_{amb} = 25 \text{ °C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
Reverse voltage		V <sub>R</sub>	5	V			
Forward current		I <sub>F</sub>	100	mA			
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I <sub>FM</sub>	200	mA			
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	А			
Power dissipation		Pv	190	mW			
Junction temperature		Tj	100	°C			
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C			
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C			
Soldering temperature	$t \leq 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C			
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W			







### **VSLY5850**



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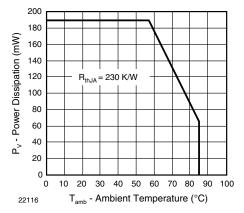


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

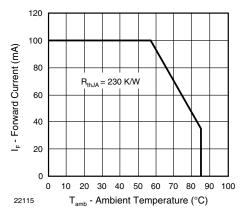


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTIC	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_{\rm F} = 100$ mA, $t_{\rm p} = 20$ ms	V <sub>F</sub>		1.65	1.9	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.9		V
Temperature coefficient of $V_F$	$I_F = 1 \text{ mA}$	TK <sub>VF</sub>		- 1.45		mV/K
	I <sub>F</sub> = 10 mA	TK <sub>VF</sub>		- 1.25		mV/K
Reverse current		I <sub>R</sub>	not designed for reverse operation			μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	Cj		125		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	l <sub>e</sub>	300	600	900	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>		5100		mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	фе		55		mW
Temperature coefficient of $\phi_{\text{e}}$	I <sub>F</sub> = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 3		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λρ	840	850	870	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		30		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I <sub>F</sub> = 100 mA	tr		10		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		10		ns



# High Speed Infrared Emitting Diode, Vishay Semiconductors 850 nm, Surface Emitter Technology

#### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

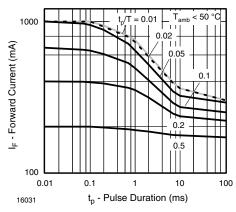


Fig. 3 - Pulse Forward Current vs. Pulse Duration

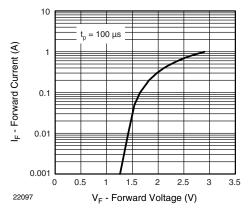


Fig. 4 - Forward Current vs. Forward Voltage

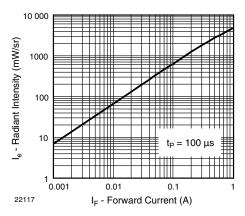


Fig. 5 - Radiant Intensity vs. Forward Current

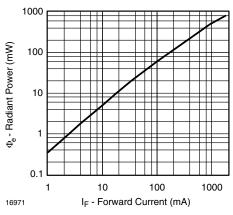


Fig. 6 - Radiant Power vs. Forward Current

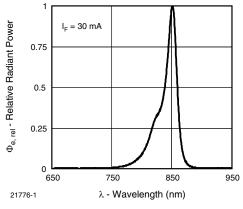


Fig. 7 - Relative Radiant Power vs. Wavelength

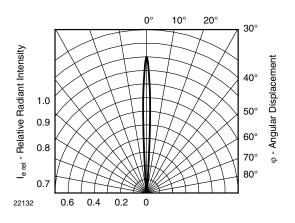
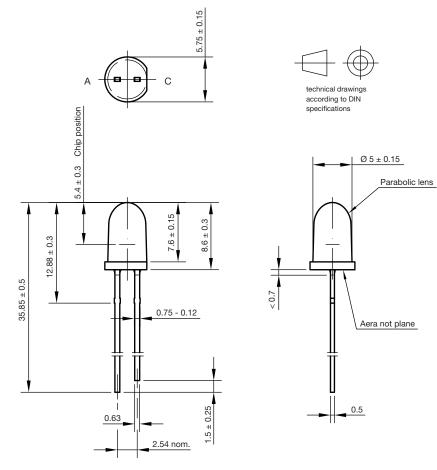


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



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### **PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5385.01-4 Issue: 2; 08.03.10 20531

Not indicated tolerances  $\pm \ 0.1$ 



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